VS-UFB170FA60

Vishay Semiconductors

Insulated Ultrafast Rectifier Module, 170 A



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PRIMARY CHARACTERISTICS					
V _R	600 V				
$I_{F(AV)}$ per module at T_{C} = 76 °C	170 A				
t _{rr}	60 ns				
Туре	Modules - diode FRED Pt®				
Package	SOT-227				

FEATURES

- Two fully independent diodes
- · Fully insulated package
- Ultrafast, soft reverse recovery, with high operation junction temperature (T_{.1} max. = 175 °C)
- Very low forward voltage drop
- · Optimized for power conversion: welding and industrial SMPS applications
- · Easy to use and parallel
- Industry standard outline
- UL approved file E78996
- Designed and gualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

The VS-UFB170FA60 insulated modules integrate two state of the art ultrafast recovery rectifiers in the compact, industry standard SOT-227 package. The diodes structure, and its life time control, provide an ultrasoft recovery current shape, together with the best overall performance, ruggedness and reliability characteristics.

These devices are thus intended for high frequency applications in which the switching energy is designed not to be predominant portion of the total energy, such as in the output rectification stage of welding machines, SMPS, DC/DC converters. Their extremely optimized stored charge and low recovery current reduce both over dissipation in the switching elements (and snubbers) and EMI/RFI.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		600	V	
Continuous forward current per diode	lF	T _C = 90 °C	94	Α	
Single pulse forward current per diode	I _{FSM}	T _C = 25 °C	850	A	
Maximum power dissipation per module	PD	T _C = 90 °C	233	W	
RMS isolation voltage	VISOL	Any terminal to case, t = 1 min	2500	V	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	



RoHS COMPLIANT



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ELECTRICAL SPECIFICATIONS PER DIODE ($T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-	
Forward voltage, per leg	V _{FM}	I _F = 50 A	-	1.02	1.19	
		I _F = 50 A, T _J = 175 °C	-	0.87	-	V
		I _F = 100 A	-	1.17	1.43	
		I _F = 100 A, T _J = 175 °C	-	1.03	-	
Reverse leakage current, per leg	I _{RM}	$V_{R} = V_{R}$ rated	-	0.5	50	μA
neverse leakage current, per leg		$T_J = 175 \text{ °C}, V_R = V_R \text{ rated}$	-	0.1	2	mA
Junction capacitance, per leg	CT	V _R = 600 V	-	43	-	pF

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		T_J = 25 °C, I_F = 1 A dI_F/dt = 200 A/µs V_R = 30 V		-	60	-	
Reverse recovery time, per leg	t _{rr}	T _J = 25 °C		-	170	-	ns
		T _J = 125 °C		-	270	-	
Dool room ourrent nor log	1	T _J = 25 °C	I _F = 25 A dI _F /dt = 500 A/μs V _R = 200 V	-	40	-	A
Peak recovery current, per leg	I _{RRM}	T _J = 125 °C		-	54	-	
Powerze receivery charge, per leg	0	T _J = 25 °C		-	3.4	-	μC
Reverse recovery charge, per leg	Q _{rr}	T _J = 125 °C		-	6.8	-	
	+	T _J = 25 °C	I _F = 50 A dI _F /dt = 500 A/μs V _R = 200 V	-	220	-	ns
Reverse recovery time, per leg	t _{rr}	T _J = 125 °C		-	300	-	
Peak recovery current, per leg		T _J = 25 °C		-	47	-	A
	I _{RRM}	T _J = 125 °C		-	61	-	
R	0	T _J = 25 °C		-	5.2	-	
Reverse recovery charge, per leg	Q _{rr}	T _J = 125 °C		-	9.1	-	μC

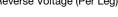
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	D		-	-	0.73	
Junction to case, both leg conducting	R _{thJC}		-	-	0.365	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.10	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				S	OT-227	

Revision: 18-Sep-2018 Document Number: 94814 2 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

VS-UFB170FA60 www.vishay.com **Vishay Semiconductors** 1000 1000 I_F - Instantaneous Forward Current (A) $T_J = 175 \ ^\circ C$ 100 I_R - Reverse Current (µA) 10 T_J = 125 °C 100 1 175 °C 0.1 = 125 °C 10 T_J = 25 °C 0.01 T_J = 25 °C 0.001 0.0001 1 200 300 500 600 0 0 100 400 0.5 1.0 1.5 2.0 2.5 V_F - Forward Voltage Drop (V) V_R - Reverse Voltage (V)

Fig. 1 - Typical Forward Voltage Drop Characteristics (Per Leg)

Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)



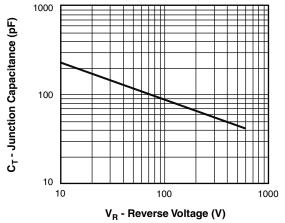
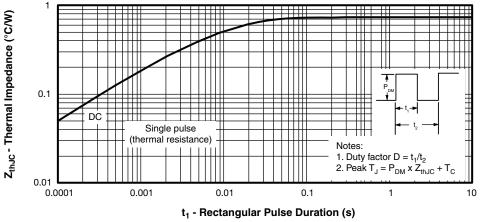


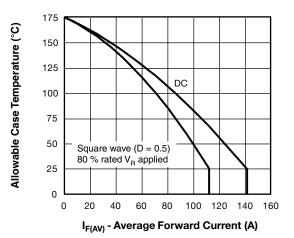
Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)







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Fig. 5 - Allowable Case Temperature vs. Average Forward Current (Per Leg)

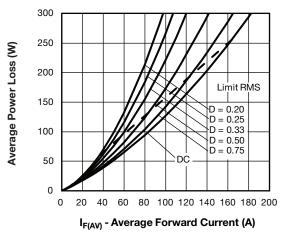


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

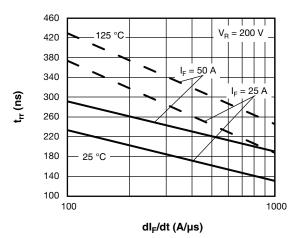


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

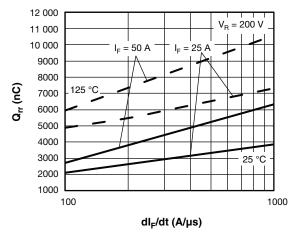


Fig. 8 - Typical Stored Charge vs. dl_F/dt (Per Leg)

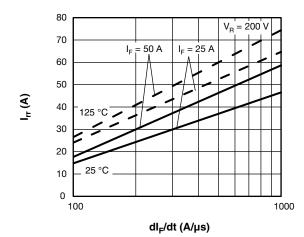


Fig. 9 - Typical Recovery Current vs. dl_F/dt (Per Leg)

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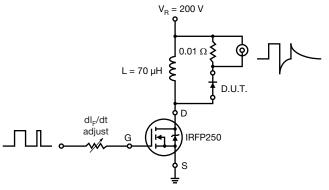
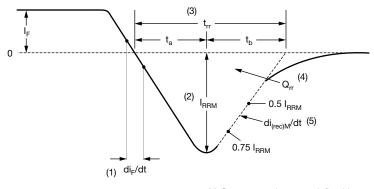


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (4) ${\rm Q}_{\rm rr}$ area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) $di_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

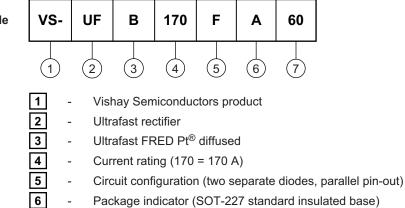
Fig. 11 - Reverse Recovery Waveform and Definitions





ORDERING INFORMATION TABLE

Device code



- Package indicator (SOT-227 standard insulated base)
- Voltage rating (60 = 600 V)

CIRCUIT CONFIGURATION					
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING			
Two separate diodes, parallel pin-out	F	Lead Assignment 4 1 1 1 1 1 1 1 1 1 1 1 1 1			

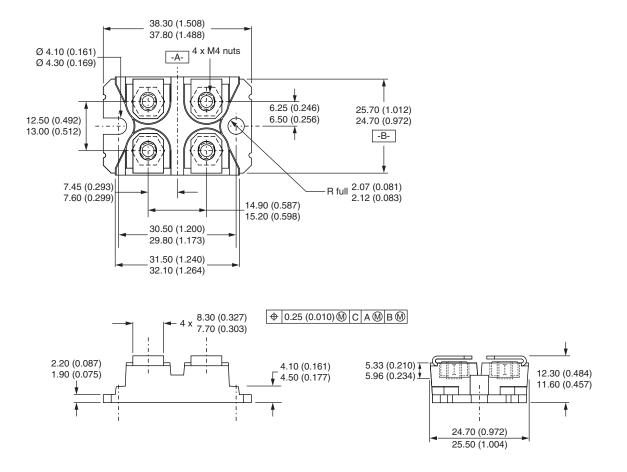
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95423					
Packaging information	www.vishay.com/doc?95425				





SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

• Controlling dimension: millimeter



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